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Non-linear structural and surface morphological modifications due to gamma irradiation in p-type porous silicon(Article)

Pandaram, P., Saranya, A., Jothi, S., Lawrence, B., Prithivikumaran, N., Jeyakumaran, N.

^aTLD Lab, Kudankulam Nuclear Power Project, Tirunelveli, Tamil Nadu 627106, India^bKarpagam Academy of Higher Education, Coimbatore, Tamil Nadu 641021, India^cV.H.N. Senthikumara Nadar College (Autonomous), Virudhunagar, Tamil Nadu 626 001, India

Abstract

The effect of gamma irradiation on the morphology and electrical properties of p-type porous silicon prepared by electro-chemical etching is investigated after total irradiation dose of 0.5Gy, 2Gy, 5Gy and 10Gy by gamma radiation from the ¹³⁷Cs radiation source. Structural changes are studied with the support of X-Ray Diffraction, Scanning Electron Microscope, Fourier Transform Infra-Red spectroscopy, Atomic Force Microscope and the electrical property changes are investigated by I-V characterization. X-Ray Diffraction peak at Si(400) showed peak broadening with increasing gamma dose. The size of crystallite in the P-Si samples as prepared is 119.54 nm and it is reduced to 14.79 nm for the P-Si sample irradiated with the gamma dose of 10 Gy. The irradiated P-Si samples show a non-linear reduction in crystallite size and exhibit radiation hardness for the total gamma irradiation dose ≤ 5Gy. Scanning Electron Microscope images of the irradiated P-Si revealed a wide variation in pore diameter from 14.794 nm to 105.324 nm for the gamma dose increased from 0.5 Gy to 10 Gy. Roughness in the irradiated sample decreased with increase in gamma dose. The change in the structural properties of the irradiated P-Si samples is nonlinear while the electrical property is linear with the increase of gamma dose and dependent on the total gamma dose. © 2019 Elsevier Ltd

Author keywords

Atomic Force Microscope Dislocation density Gamma irradiation Gray p-type porous silicon Porous silicon Roughness Total irradiation dose

Indexed keywords

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Atomic force microscopy Crystal atomic structure Crystallite size Etching Irradiation Morphology Porous silicon Scanning electron microscopy Silicon compounds Surface roughness X ray diffraction

Engineering uncontrolled terms

Dislocation densities Gamma irradiation Gray Irradiation dose P-type

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Gamma rays

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